MITSUBISHI HYBRID IC

M57161L-01

FOR DRIVING TRENCH-GATE IGBT

DESCRIPTION

M57161L-01 is a hybrid IC designed to drive trenchgate IGBT module with built in RTC.

This device can operate by an input of +15V because of electrical isolation between the input and output by an opto coupler, and the built in DC-DC converter isolated between a pair of positive/negative outputs for gate driving.

With built in protection circuits, this devices can maintain a reverse bias for a predetermined time after the detection of an over current(short circuit). Therefore, the protective system operates with a margin of time.

The over current(short circuit) detector functions with RTC circuit built in IGBT module to detect a drop of gate voltage.

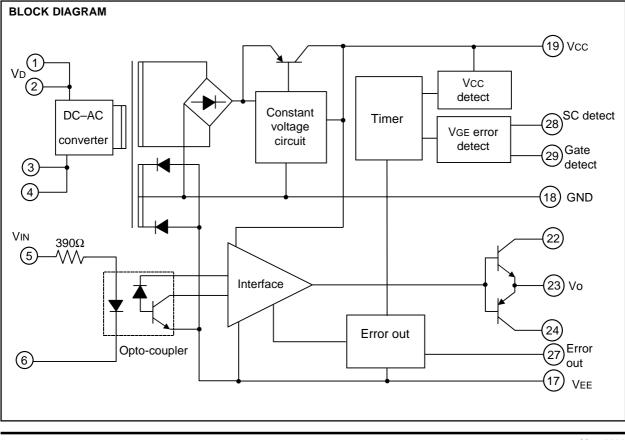
Recommend module ; IGBT module (F)series

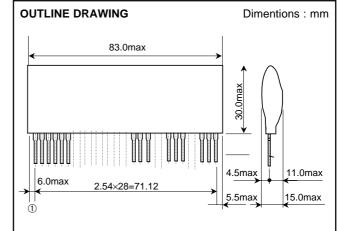
FEATURES

- Built in insulated DC-DC converter for IGBT drive
- Built in short circuit protection circuit
- Electrical isolation between input and output with opto-coupler (Vios=2500Vrms for 1minute)

APPLICATION

To drive IGBT module for inverter or AC servo systems application







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ABSOLUTE MAXIMUM RATINGS (Unless otherwise specified, Ta = 25°C)

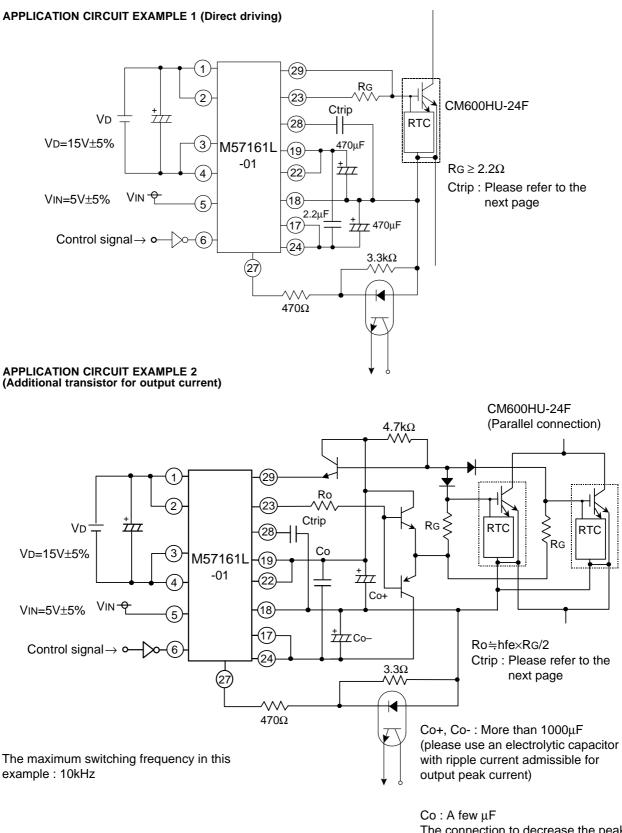
Symbol	Parameter	Conditions	Ratings	Units
Vd	Supply voltage		16	V
Vi	Input voltages	Applied between: 5-6	-1 ~ +7	V
Vo	Output voltages	At the output voltage "H" VD=15.7V	16.5	V
Іонр	Output current	Pulse width 1µs, f≤20kHz	-7	A
IOLP			7	A
Viso	Isolation voltage	Sine-wave voltage 60Hz, 1min	2500	Vrms
Тс	Case temperature		85	°C
Topr	Operating temperature		-20 ~ +60	°C
Tstg	Storage temperature		-25 ~ +100	°C
IFO	Fault output current	Input current 27pin	25	mA
Vr	Applied 29 pin		Vcc	V

$\textbf{ELECTRICAL CHARACTERISTICS (Ta = 25^{\circ}C, VD = 15.0V, Vin = 5.0V, f = 20kHz, Rg = 2.2\Omega: CM600HU-24F)}$

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Тур.	Max.	Unit
Vd	Supply voltage	Recommended range	14.3	15.0	15.7	V
Vin	Pull-up voltage on input side	Recommended range	4.5	5.0	5.5	V
Ін	"H" Input current	Recommended range	9	10	11	MA
f	Switching frequency	Recommended range	_	—	20	kHz
Rg	Gate resistor	Recommended range	2.2	—	—	Ω
Ін	"H" Input current	VIN=5V	—	10	—	mA
Vcc	Gate + supply voltage	VIN=0V, f=0Hz	17.0	17.4	17.8	V
Vee	Gate - supply voltage	VIN=0V, f=0Hz	-5.5	-6.5	-7.5	V
Vон	"H" Output voltage		14	15.5	16.5	V
Vol	"L" Output voltage		-4.0	-5.0	-6.0	V
t PLH	"L-H" Propagation time	Iiн=10mA	_	0.4	1	μs
tr	"L-H" Rise time	IIH=10mA	_	0.4	0.5	μs
t PHL	"H-L" Propagation time	IIH=10mA	_	1.3	2.0	μs
tf	"H-L" Fall time	IIH=10mA	_	0.4	0.5	μs
t timer	Timer	Between start and cancel(Under input signal "L")	1.5	_	2.5	ms
IFO	Fault output current	Applied 27pin R=470Ω	_	12	_	mA
tc	Controlled time detect delay time	In the rise time 29pin :11V, 28pin :open	_	3.5	_	μs
t d	Short-circuit protect delay time	In the rise time 29pin :11V, 28pin :open		6.5	—	μs
VCL	Start voltage for protection at lower Vcc	The required minimum of positive power supply for gate when Vo is in the state of "H"	14.2	15.2	16.2	V
Vsc	Over-current detect voltage		11.0	11.6	12.2	V



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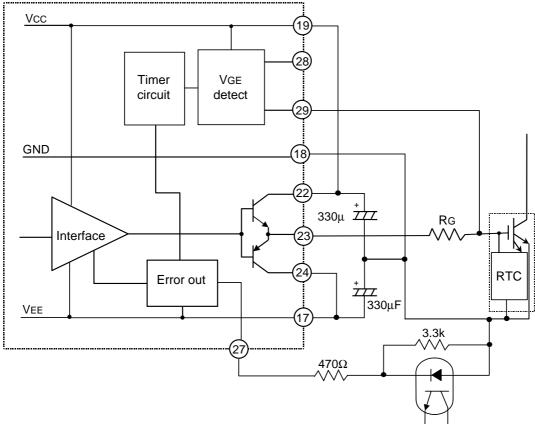


The connection to decrease the peak of ripple current

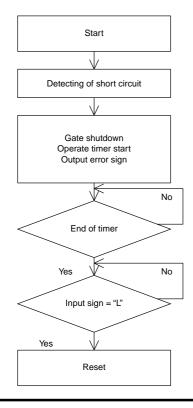


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OPERATION OF PROTECTION CIRCUIT



FLOW CHART



- 1. The VGE error detect circuit operates when an input signal is in the state of "H".
- 2. An error judgment is made when VGE becomes below Vsc (=11v : min).
- 3. The VGE error detect circuit does not function until the time when the gate voltage reaches Vsc (=12.2V : max).

The tc (= 3.5μ s) of controlled time detect short circuit is set in order to ensure the turn-on of IGBT modules.

- 4. If a rise time of gate voltage is longer than 3.5µs, the tc can be adjusted by connecting a capacitor (Ctrip) between pins 28 and 18. Please refer to td vs. Ctrip CHARACTERISTICS on page 6/6.
- 5. The td is a delay time due to signal transmission of each protection circuit.
- If short-circuit current flows at turn-on, the controlled time detect short circuit (td) is included to the td of short-circuit protect delay time. The td can be changed through Ctrip.

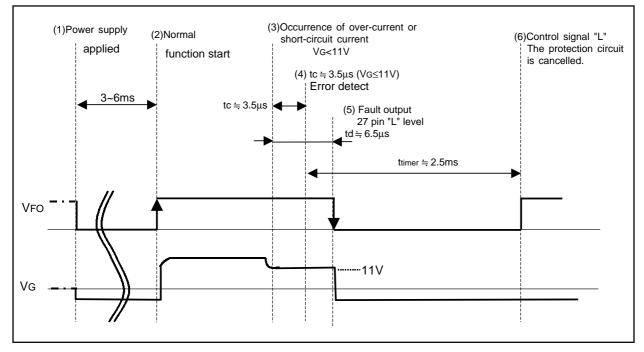
As a gate shutdown of IGBT modules within 10 μs is recommended, Ctrip should be below 220pF in order to set the maximum of td below 10 μs



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CONTROL OF IGBT MODULE DRIVER

The timing chart for control of IGBT module drivers with electrical isolation between the input and output is as follows.



Timing chart when protection circuit operates under over-current (short circuit) with power supply applied.

DESCRIPTION OF TIMING CHART

- (1) When Vcc is within 10 to 15 voltages, S/C detect output (VFO) is in the low state. The output vontage remains in the low state for 3 to 6 ms. If the power supply is applied in the high state of input signal, the output (Vo) remains in the low state. But VFO becomes in the low state for 3 to 6 ms. After normal function starts, if Vcc is below the start voltage of protection circuit (Typ. 15.2V), VFO is low and Vo is low voltage for the same period.
- (2) After VFO returns to high level, control signal shoud be applied.
- (3) If over-current or short-circuit current flows between the collector and emitter of IGBT modules, the internal RTC circuit pulls the gate voltage down below 11V
- (4) When the turn-on of IGBT coincides with over-current or short-circuit current, the timer circuit functions after tc.
- (5) After td from the short-circuit or over-current, the output voltage of Vo is low and VFO is low voltage at the same time. The output remains low during the operating time of timer circuit regardless of input signals.
- (6) If the input signal is low level after ttimer, the protection function is cancelled. And then VFO returns to high voltage.



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tPLH, tPHL vs. Ta CHARACTERISTICS **tPLH**, **tPHL vs. VI CHARACTERISTICS** (TYPICAL) (TYPICAL) PROPAGATION DELAY TIME "L-H"tpl:H(μs) PROPAGATION DELAY TIME "H-L"tpHL(μs) PROPAGATION DELAY TIME "L-H"tPLH(μs) PROPAGATION DELAY TIME "H-L"tPHL(μs) 3.0 3.0 VD = 15V RG = 2.2Ω Ta = 25°C LOAD : CM600HU-24F VD = 15V RG = 2.2Ω VIN = 5V 2.5 2.5 LOAD : CM600HU-24F 2.0 2.0 **t**PHL 1.5 1.5 tPHI 1.0 1.0 **t**PLH tPLH 0.5 0.5 0.0 L 3.0 0**∟** -40 -20 0 20 40 60 80 4.0 5.0 6.0 7.0 AMBIENT TEMPERATURE Ta (°C) INPUT SIGNAL VOLTAGE VI (V) td vs. Ta CHARACTERISTICS td vs. Ctrip CHARACTERISTICS (TYPICAL) (TYPICAL) 14 14 VD = 15V VSC = 11V Ta = 25°C VD = 15V VSC = 11V SHORT-CIRCUIT PROTECTION DELAY TIME td (µs) SHORT-CIRCUIT PROTECTION DELAY TIME td (μ s) 12 12 10 10 Ctrip = 100pF8 8 6 Ctrip = 0 6 4 4 2 2 0 **L** <u>0</u>40 -20 0 20 40 60 80 100 200 300 400 500 CONNECTIVE CAPACISTANCE AMBIENT TEMPERATURE Ta (°C) Ctrip (pF), (Pin : 28-18) POWER DISSIPATION vs. AMBIENT TEMPERATURE **DISSIPATION CURRENT vs. SUPPLY VOLTAGE** (MAXIMUM RATING) (TYPICAL) 2.5 120 Ta = 25°C INPUT SIGNAL "H" POWER DISSIPATION PD (W) DISSIPATION CURRENT (mA) 100 2 80 1.5 INPUT SIGNAL "L" 60 1 40 0.5 20 0**L** 0 L 12 20 40 60 80 100 13 14 15 16 17 AMBIENT TEMPERATURE Ta (°C) SUPPLY VOLTAGE VD (V)

MITSUBISHI ELECTRIC

CHARACTERISTICS CURVES

Mar. 2002